

RJK4012DPE

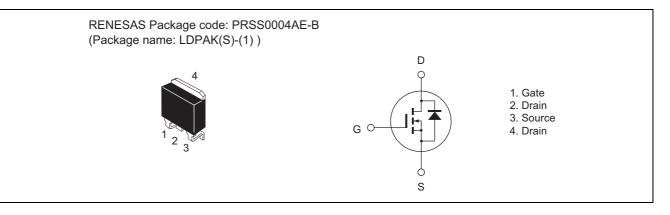
Silicon N Channel MOS FET High Speed Power Switching

> REJ03G1575-0100 Rev.1.00 Aug 08, 2007

Features

- Low on-resistance
- Low leakage current
- High speed switching

Outline



Absolute Maximum Ratings

 $(Ta = 25^{\circ}C)$ Item Symbol Ratings Unit Drain to source voltage V_{DSS} 400 V V Gate to source voltage V_{GSS} ±30 15 A Drain current I_D Note1 Drain peak current 45 A Body-drain diode reverse drain current I_{DR} 15 A 45 Body-drain diode reverse drain peak current I_{DR (pulse)} А I_{AP}Note3 Avalanche current 5 A E_{AR}^{Note3} 1.4 Avalanche energy mJ Pch Note2 W Channel dissipation 100 Channel to case thermal impedance θch-c 1.25 °C/W Channel temperature Tch 150 °C °C Storage temperature Tstg -55 to +150

Notes: 1. $PW \le 10 \ \mu s$, duty cycle $\le 1\%$

2. Value at Tc = 25°C

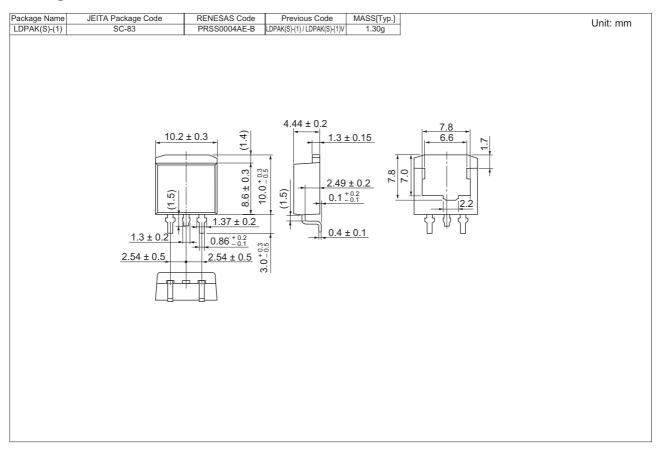
3. STch = 25° C, Tch $\leq 150^{\circ}$ C

Electrical Characteristics

						$(Ta = 25^{\circ}C)$
Item	Symbol	Min	Тур	Мах	Unit	Test conditions
Drain to source breakdown voltage	V _{(BR)DSS}	400		—	V	$I_D = 10 \text{ mA}, V_{GS} = 0$
Zero gate voltage drain current	I _{DSS}	_	—	1	μΑ	$V_{DS} = 400 \text{ V}, V_{GS} = 0$
Gate to source leak current	I _{GSS}		—	±0.1	μΑ	$V_{GS} = \pm 30$ V, $V_{DS} = 0$
Gate to source cutoff voltage	V _{GS(off)}	3.0	—	4.5	V	$V_{DS} = 10 \text{ V}, I_D = 1 \text{ mA}$
Static drain to source on state resistance	R _{DS(on)}		0.34	0.41	Ω	$I_D = 7.5 \text{ A}, V_{GS} = 10 \text{ V}^{\text{Note4}}$
Input capacitance	Ciss	_	1100	_	pF	V _{DS} = 25 V
Output capacitance	Coss	_	135	—	pF	V _{GS} = 0 f = 1 MHz
Reverse transfer capacitance	Crss		17	_	pF	
Turn-on delay time	t _{d(on)}		30	_	ns	I _D = 7.5 A
Rise time	tr	_	29	—	ns	V _{GS} = 10 V
Turn-off delay time	t _{d(off)}	_	77	—	ns	R _L = 26.7 Ω Rg = 10 Ω
Fall time	t _f	_	19	—	ns	
Total gate charge	Qg		29	—	nC	V _{DD} = 320 V
Gate to source charge	Qgs	_	5.5	—	nC	V _{GS} = 10 V I _D = 15 A
Gate to drain charge	Qgd	—	13	—	nC	
Body-drain diode forward voltage	V _{DF}	—	0.91	1.55	V	$I_F = 15 \text{ A}, V_{GS} = 0^{Note4}$
Body-drain diode reverse recovery time	t _{rr}		260		ns	$I_F = 15 \text{ A}, V_{GS} = 0$ $di_F/dt = 100 \text{ A}/\mu \text{s}$

Notes: 4. Pulse test

Package Dimensions



Ordering Information

Part No.	Quantity	Shipping Container
RJK4012DPE-00-J3	1000 pcs	Taping

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